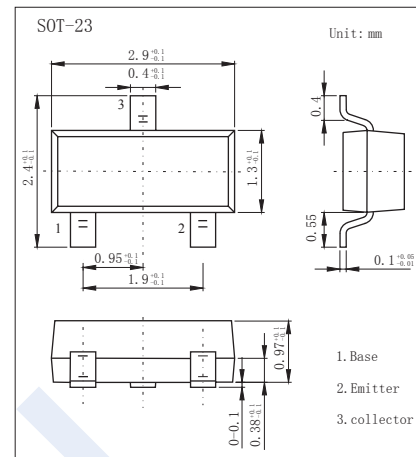


## PNP Transistors

### 2SA1122



#### ■ Features

- Low frequency amplifier

#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-55	V
Collector to emitter voltage	$V_{CEO}$	-55	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-55			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}, R_{BE} = \infty$	-55			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -30\text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4\text{ V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current transfer ratio	$h_{FE}$	$V_{CE} = -12\text{ V}, I_C = -2\text{ mA}$	160		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$			-0.5	V
Base to emitter voltage	$V_{BE}$	$V_{CE} = -12\text{ V}, I_C = -2\text{ mA}$			-0.75	V

#### ■ $h_{FE}$ Classification

Marking	CC	CD	CE
$h_{FE}$	160~320	250~500	400~800

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#### ■ Typical Characteristics

